

**isc N-Channel MOSFET Transistor**
**IXFQ30N60X**
**• FEATURES**

- Drain Source Voltage-  
:  $V_{DSS} = 600V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} \leq 155m\ \Omega @ V_{GS} = 10V$
- Fast Switching
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• APPLICATIONS**

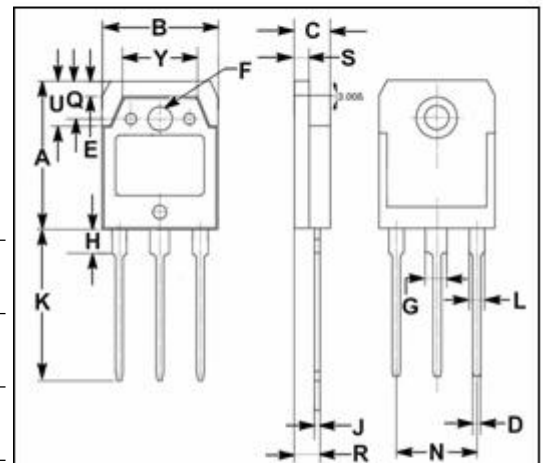
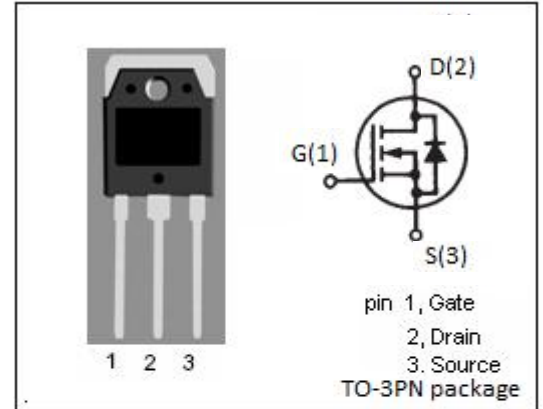
- Easy to Mount
- Space Savings
- High Power Density

**• ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	600	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 30$	V
$I_D$	Drain Current-Continuous	30	A
$I_{DM}$	Drain Current-Single Plused	60	A
$P_D$	Total Dissipation @ $T_c=25^\circ\text{C}$	500	W
$T_j$	Max. Operating Junction Temperature	-55~150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$

**• THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	0.25	$^\circ\text{C}/\text{W}$



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

## isc N-Channel MOSFET Transistor

## IXFQ30N60X

## • ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 250uA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 4mA	2.5		4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 15A			155	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0 V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0; T <sub>J</sub> =125°C			25 750	μA
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>F</sub> = 30A; V <sub>GS</sub> = 0			1.4	V

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